

ETCHING METHOD AND PLASMA PROCESSING APPARATUS

ABSTRACT

5 An etching method includes (a) providing a substrate on a substrate support in a chamber, the substrate including a first region and a second region, the first region including a first material including at least one selected from the group consisting of silicon oxide and carbon, and the second region including a second material different from the first material; and (b) exposing the substrate to first plasma generated from a first process gas including hydrogen fluoride without supplying electric bias to the substrate support.

Fig. 3